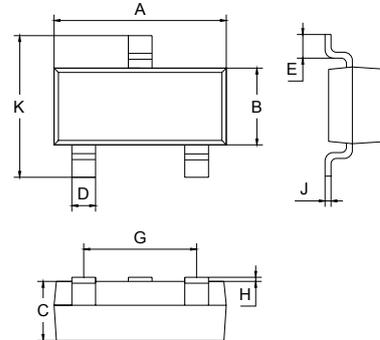


1. BASE
2. EMITTER
3. COLLECTOR

### FEATURES

- Epitaxial planar die construction.
- Complementary PNP type available (MMBT3906).
- Collector Current Capability  $I_{CM} = 200\text{mA}$ .
- Collector-emitter Voltage  $V_{CEO} = 40\text{V}$ .



| SOT-23               |             |      |
|----------------------|-------------|------|
| Dim                  | Min         | Max  |
| A                    | 2.70        | 3.10 |
| B                    | 1.10        | 1.50 |
| C                    | 1.0 Typical |      |
| D                    | 0.4 Typical |      |
| E                    | 0.35        | 0.48 |
| G                    | 1.80        | 2.00 |
| H                    | 0.02        | 0.1  |
| J                    | 0.1 Typical |      |
| K                    | 2.20        | 2.60 |
| All Dimensions in mm |             |      |

### APPLICATIONS

- General switching and amplification

### ORDERING INFORMATION

| Type No.    | Marking | Package Code |
|-------------|---------|--------------|
| MMBT3904LT1 | 1AM     | SOT-23       |

### MAXIMUM RATING @ $T_a = 25^\circ\text{C}$ unless otherwise specified

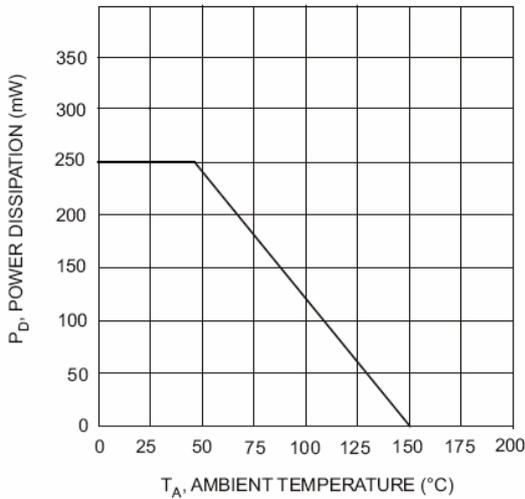
| SYMBOL    | PARAMETER                     | CONDITIONS                      | Value       | UNIT             |
|-----------|-------------------------------|---------------------------------|-------------|------------------|
| $V_{CBO}$ | collector-base voltage        | open emitter                    | 60          | V                |
| $V_{CEO}$ | collector-emitter voltage     | open base                       | 40          | V                |
| $V_{EBO}$ | emitter-base voltage          | open collector                  | 6           | V                |
| $I_C$     | collector current (DC)        |                                 | 100         | mA               |
| $I_{CM}$  | peak collector current        |                                 | 200         | mA               |
| $I_{BM}$  | peak base current             |                                 | 100         | mA               |
| $P_{tot}$ | total power dissipation       | $T_{amb} \leq 25^\circ\text{C}$ | 250         | mW               |
| $T_{stg}$ | storage temperature           |                                 | -65 to +150 | $^\circ\text{C}$ |
| $T_j$     | junction temperature          |                                 | 150         | $^\circ\text{C}$ |
| $T_{amb}$ | operating ambient temperature |                                 | -65 to +150 | $^\circ\text{C}$ |

### ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

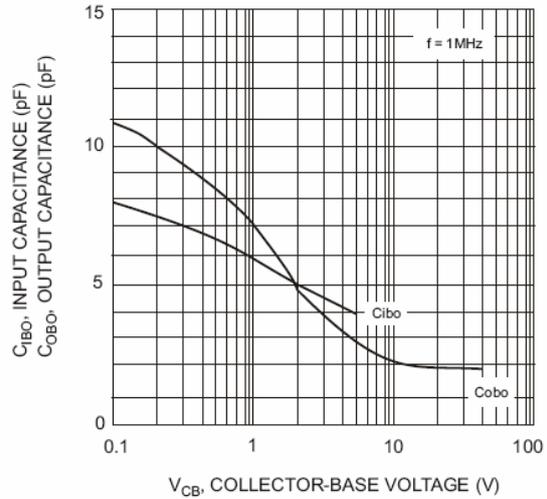
| SYMBOL  | PARAMETER                            | CONDITIONS   | MIN. | MAX. | UNIT |
|---|--------------------------------------|--|------|------|------|
| $I_{CBO}$                                     | collector cut-off current            | $I_E = 0; V_{CB} = 30\text{ V}$  | -    | 50   | nA   |
| $I_{EBO}$                                     | emitter cut-off current              | $I_C = 0; V_{EB} = 6\text{ V}$   | -    | 50   | nA   |
| $h_{FE}$                                      | DC current gain                      | $V_{CE} = 1\text{ V};$<br>$I_C = 0.1\text{mA}$   | 60   | -    |      |
|   |                                      | $I_C = 1\text{mA}$   | 80   | -    |      |
|   |                                      | $I_C = 10\text{mA}$  | 100  | 300  |      |
|   |                                      | $I_C = 50\text{mA}$  | 60   | -    |      |
|   |                                      | $I_C = 100\text{mA}$   | 30   | -    |      |
| $V_{CE(sat)}$                                 | collector-emitter saturation voltage | $I_C = 10\text{mA}; I_B = 1\text{mA}$  | -    | 200  | mV   |
|   |                                      | $I_C = 50\text{mA}; I_B = 5\text{mA}$  | -    | 300  | mV   |
| $V_{BE(sat)}$                                 | base-emitter saturation voltage      | $I_C = 10\text{mA}; I_B = 1\text{mA}$  | 650  | 850  | mV   |
|   |                                      | $I_C = 50\text{mA}; I_B = 5\text{mA}$  | -    | 950  | mV   |
| $C_{obo}$                                     | Output Capacitance                   | $I_E = I_e = 0; V_{CB} = 5\text{V};$<br>$f = 1\text{MHz}$  | -    | 4    | pF   |
| $C_{ibo}$                                     | Input Capacitance                    | $I_C = I_c = 0; V_{BE} = 500\text{mV};$<br>$f = 1\text{MHz}$   | -    | 8    | pF   |
| $f_T$   | transition frequency                 | $I_C = 10\text{mA}; V_{CE} = 20\text{V};$<br>$f = 100\text{MHz}$   | 300  | -    | MHz  |
| F   | noise figure                         | $I_C = 100\text{mA}; V_{CE} = 5\text{V};$<br>$R_S = 1\text{k}\Omega; f = 10\text{Hz to } 15.7\text{kHz}$ | -    | 5    | dB   |
| Switching times (between 10% and 90% levels); |                                      |  |      |      |      |
| $t_d$   | delay time                           | $I_{Con} = 10\text{mA}; I_{Bon} = 1\text{mA};$<br>$I_{Boff} = -1\text{mA}$                               | -    | 35   | ns   |
| $t_r$   | rise time                            |  | -    | 35   | ns   |
| $t_s$   | storage time                         |  | -    | 200  | ns   |
| $t_f$   | fall time                            |  | -    | 50   | ns   |

Note Pulse test:  $t_p \leq 300\text{ ms}; d \leq 0.02$ .

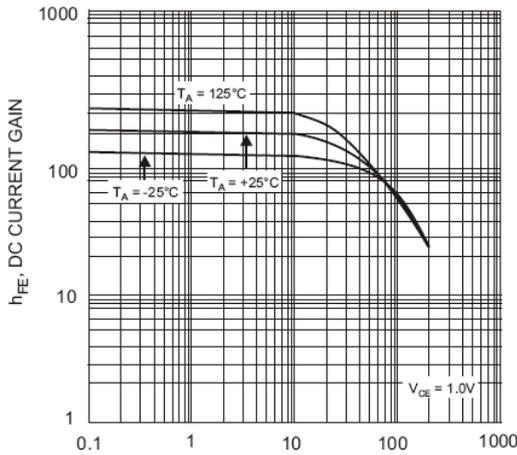
### TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



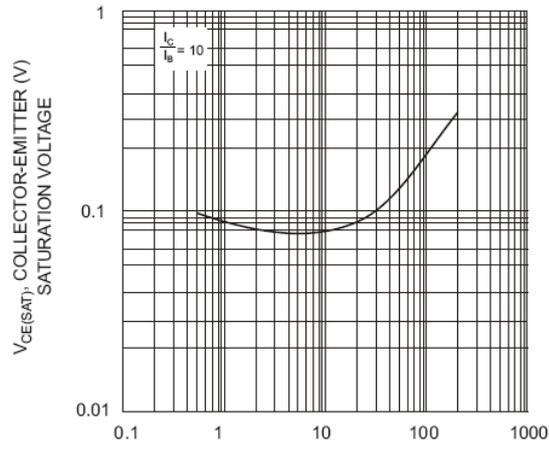
$T_A$ , AMBIENT TEMPERATURE ( $^\circ\text{C}$ )  
Fig. 1, Max Power Dissipation vs Ambient Temperature



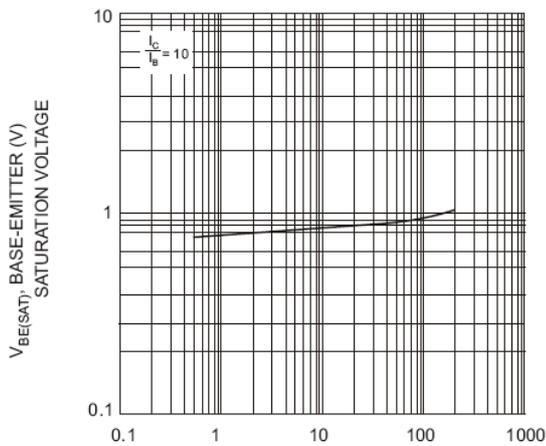
$V_{CB}$ , COLLECTOR-BASE VOLTAGE (V)  
Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage



$I_C$ , COLLECTOR CURRENT (mA)  
Fig. 3, Typical DC Current Gain vs Collector Current



$I_C$ , COLLECTOR CURRENT (mA)  
Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current



$I_C$ , COLLECTOR CURRENT (mA)  
Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current

| Device      | Package | Shipping       |
|-------------|---------|----------------|
| MMBT3904LT1 | SOT-23  | 3000/Tape&Reel |

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [Bipolar Transistors - BJT category](#):*

*Click to view products by [LGE manufacturer](#):*

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [MJ15024/WS](#) [MJ15025/WS](#) [BC546/116](#) [BC556/FSC](#) [BC557/116](#) [BSW67A](#) [HN7G01FU-A\(T5L,F,T](#)  
[NJVMJD148T4G](#) [NSVMMBT6520LT1G](#) [NTE187A](#) [NTE195A](#) [NTE2302](#) [NTE2330](#) [NTE2353](#) [NTE316](#) [IMX9T110](#) [NTE63](#) [NTE65](#)  
[C4460](#) [SBC846BLT3G](#) [2SA1419T-TD-H](#) [2SA1721-O\(TE85L,F\)](#) [2SA1727TLP](#) [2SA2126-E](#) [2SB1202T-TL-E](#) [2SB1204S-TL-E](#) [2SC5488A-](#)  
[TL-H](#) [2SD2150T100R](#) [SP000011176](#) [FMC5AT148](#) [2N2369ADCSM](#) [2SB1202S-TL-E](#) [2SC2412KT146S](#) [2SC4618TLN](#) [2SC5490A-TL-H](#)  
[2SD1816S-TL-E](#) [2SD1816T-TL-E](#) [CMXT2207 TR](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#) [BC557B](#) [TTC012\(Q\)](#) [BULD128DT4](#) [JANTX2N3810](#)  
[Jantx2N5416](#) [US6T6TR](#) [KSF350](#) [068071B](#)